



## ACJT810-10H 8A TRIACs

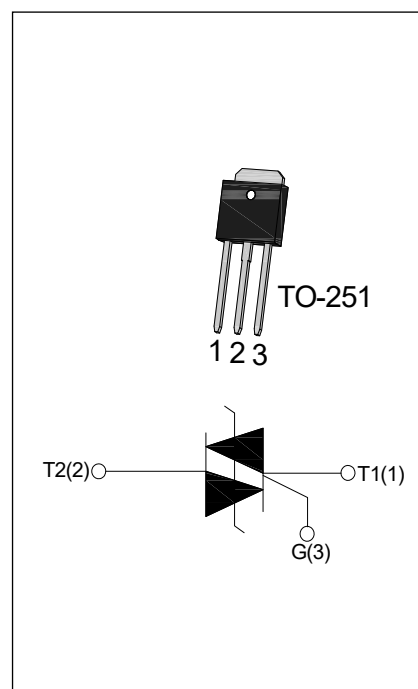
Rev.1

### DESCRIPTION:

The ACJT810-10H of double mesa technology provide high interference immunity, They can be used as an static ON/OFF function in electrical control system, and used as a driver of low power and high inductance or resistive loads, such as jet pumps of dishwashers, fans of air-conditioner ... Package TO-251 is RoHS compliant. (2011/65/EU)

### MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	8	A
$V_{DRM}/V_{RRM}$	1000	V
$I_{GT1-3}$	$\leq 10$	mA



### ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		$T_{stg}$	-40-150	$^{\circ}C$
Operating junction temperature range		$T_j$	-40-125	$^{\circ}C$
Repetitive peak off-state voltage( $T_j=25^{\circ}C$ )		$V_{DRM}$	1000	V
Repetitive peak reverse voltage( $T_j=25^{\circ}C$ )		$V_{RRM}$	1000	V
Non repetitive surge peak Off-state voltage		$V_{DSM}$	$V_{DRM} + 100$	V
Non repetitive peak reverse voltage		$V_{RSM}$	$V_{RRM} + 100$	V
RMS on-state current	TO-251 ( $T_C=95^{\circ}C$ )	$I_{T(RMS)}$	8	A
Non repetitive surge peak on-state current (full cycle, F=50Hz)		$I_{TSM}$	80	A
$I^2t$ value for fusing ( $t_p=10ms$ )		$I^2t$	32	$A^2s$
Rate of rise of on-state current ( $I_G=2 \times I_{GT}$ )		$di_T/dt$	50	$A/\mu s$
Peak gate current		$I_{GM}$	1	A
Average gate power dissipation		$P_{G(AV)}$	0.1	W
Peak gate power		$P_{GM}$	1	W

ELECTRICAL CHARACTERISTICS ( $T_j=25^{\circ}\text{C}$  unless otherwise specified)

Symbol	Test Condition	Quadrant		Value	Unit
$I_{GT}$	$V_D=12\text{V}$ $R_L=33\Omega$	I - II -III	MAX	10	mA
$V_{GT}$		I - II -III	MAX	1.3	V
$V_{GD}$	$V_D=V_{DRM}$ $T_j=125^{\circ}\text{C}$ $R_L=3.3\text{K}\Omega$	I - II -III	MIN	0.2	V
$I_L$	$I_G=1.2I_{GT}$	I -III	MAX	25	mA
		II		30	
$I_H$	$I_T=100\text{mA}$		MAX	15	mA
dv/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^{\circ}\text{C}$		MIN	600	V/ $\mu\text{s}$

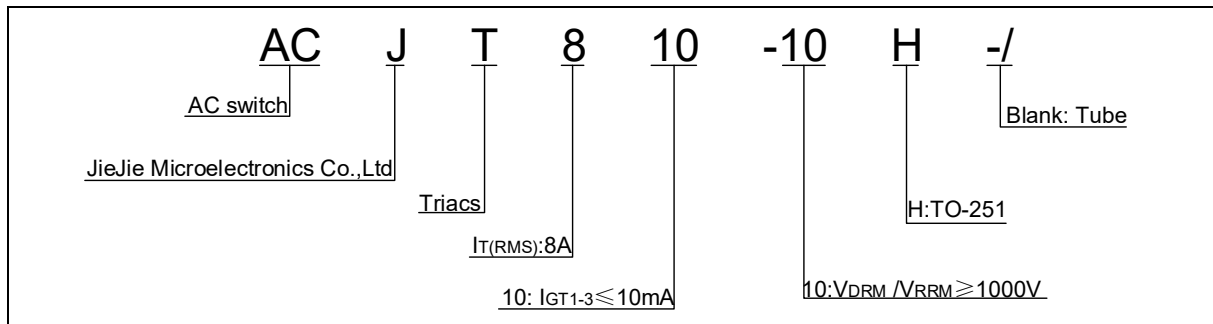
## STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
$V_{TM}$	$I_{TM}=11\text{A}$ $t_p=380\mu\text{s}$	$T_j=25^{\circ}\text{C}$	1.55	V
$V_{TO}$	Threshold voltage	$T_j=125^{\circ}\text{C}$	0.99	V
$R_d$	Dynamic resistance	$T_j=125^{\circ}\text{C}$	41	m $\Omega$
$I_{DRM}$	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^{\circ}\text{C}$	5	$\mu\text{A}$
$I_{RRM}$		$T_j=125^{\circ}\text{C}$	1	mA

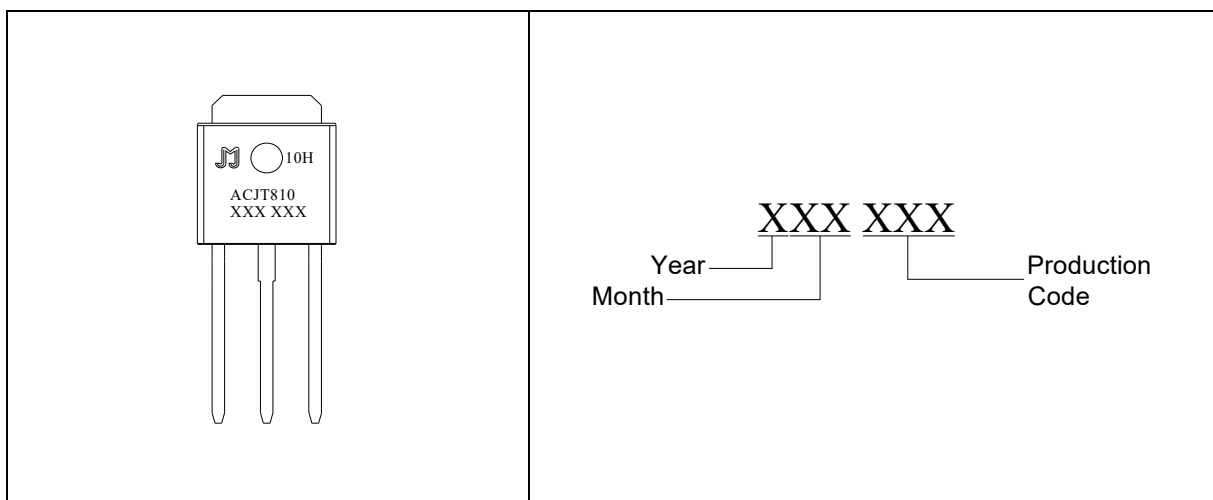
## THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-251	2.5	$^{\circ}\text{C}/\text{W}$

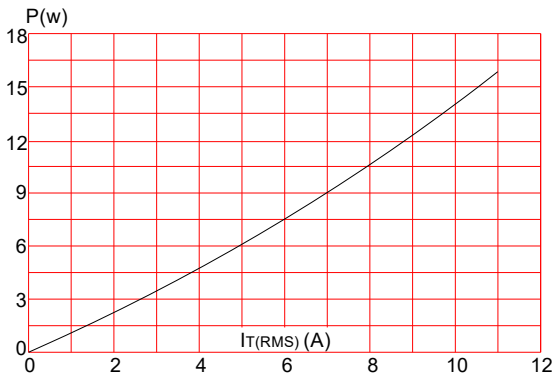
## ORDERING INFORMATION



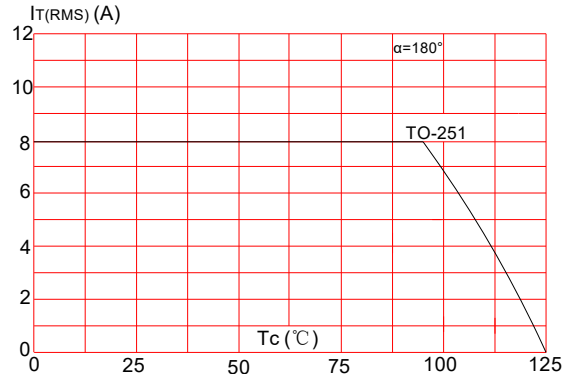
## MARKING



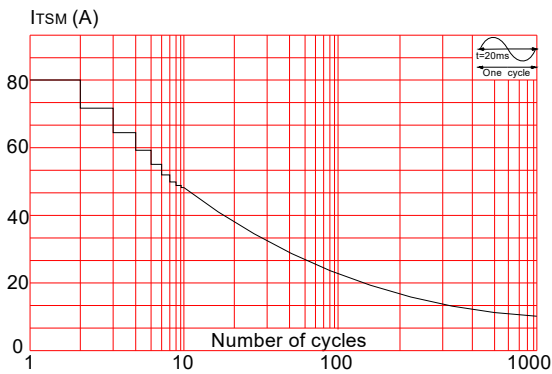
**FIG.1** Maximum power dissipation versus RMS on-state current



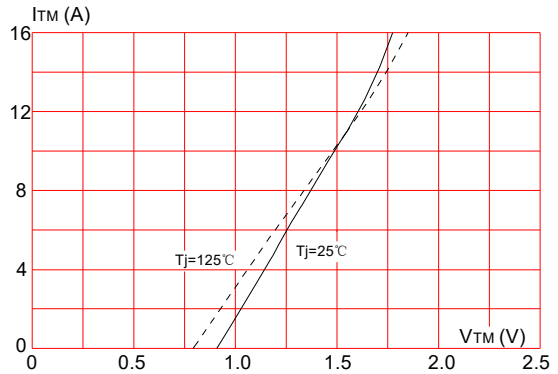
**FIG.2:** RMS on-state current versus case temperature



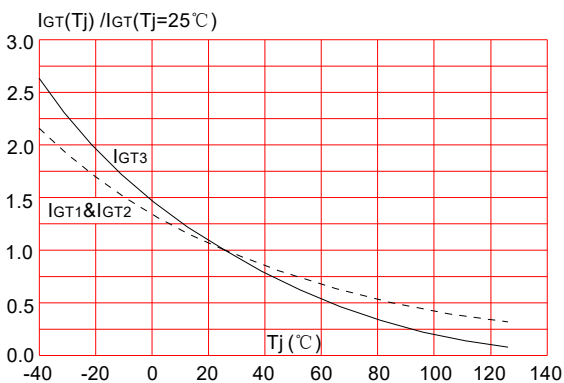
**FIG.3:** Surge peak on-state current versus number of cycles



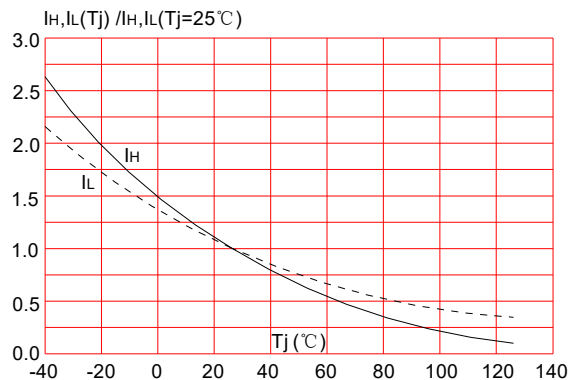
**FIG.4:** On-state characteristics (maximum values)



**FIG.5:** Relative variations of gate trigger current versus junction temperature



**FIG.6:** Relative variations of holding current, latching current versus junction temperature



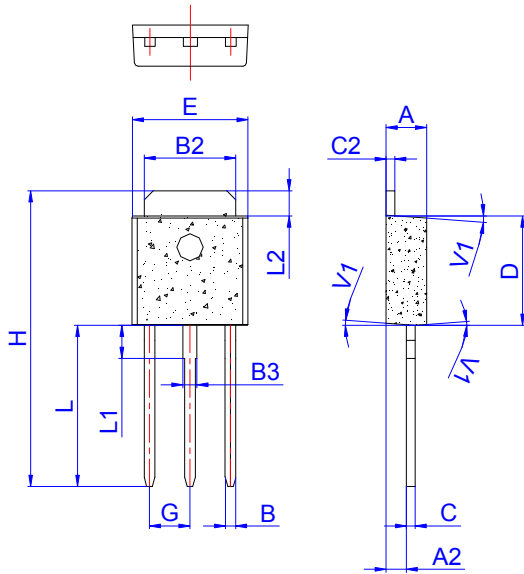
## ORDERING INFORMATION

Order code	Voltage $V_{DRM}/V_{RRM}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
ACJT810-10H	1000	$\leq 10$	TO-251	80	Tube

## Document Revision History

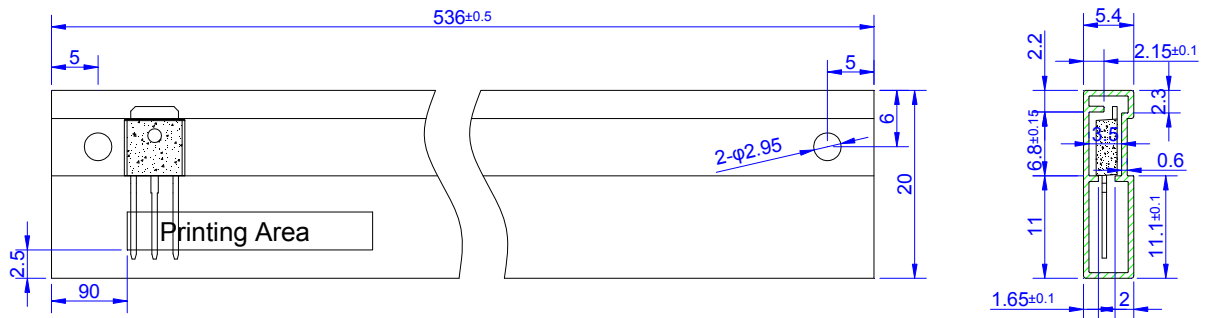
Date	Revision	Changes
Mar 18, 2022	1	Last update

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	0.90		1.20	0.035		0.047
B	0.55		0.65	0.022		0.026
B2	5.10		5.40	0.200		0.213
B3	0.76		0.85	0.030		0.033
C	0.45		0.62	0.018		0.024
C2	0.48		0.62	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.70	0.252		0.264
G		2.30			0.091	
H	16.0		17.0	0.630		0.669
L	8.90		9.40	0.350		0.370
L1	1.80		1.90	0.071		0.075
L2	1.37		1.50	0.054		0.059
V1		4°			4°	

DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-251	TUBE	80	4,000	20,000



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